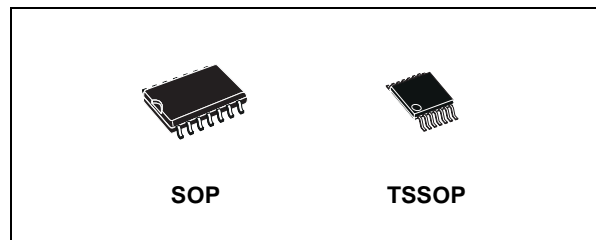


TRIPLE 3-INPUT NAND GATE

- HIGH SPEED:
 $t_{PD} = 5.3ns$ (TYP.) at $V_{CC} = 3.3V$
- COMPATIBLE WITH TTL OUTPUTS
- LOW POWER DISSIPATION:
 $I_{CC} = 2\mu A$ (MAX.) at $T_A = 25^\circ C$
- LOW NOISE:
 $V_{OLP} = 0.3V$ (TYP.) at $V_{CC} = 3.3V$
- 75Ω TRANSMISSION LINE DRIVING CAPABILITY
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 12mA$ (MIN) at $V_{CC} = 3.0V$
- PCI BUS LEVELS GUARANTEED AT 24 mA
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \approx t_{PHL}$
- OPERATING VOLTAGE RANGE:
 $V_{CC}(OPR) = 2V$ to $3.6V$ (1.2V Data Retention)
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 10
- IMPROVED LATCH-UP IMMUNITY

DESCRIPTION

The 74LVQ10 is a low voltage CMOS TRIPLE 3-INPUT NAND GATE fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS



ORDER CODES

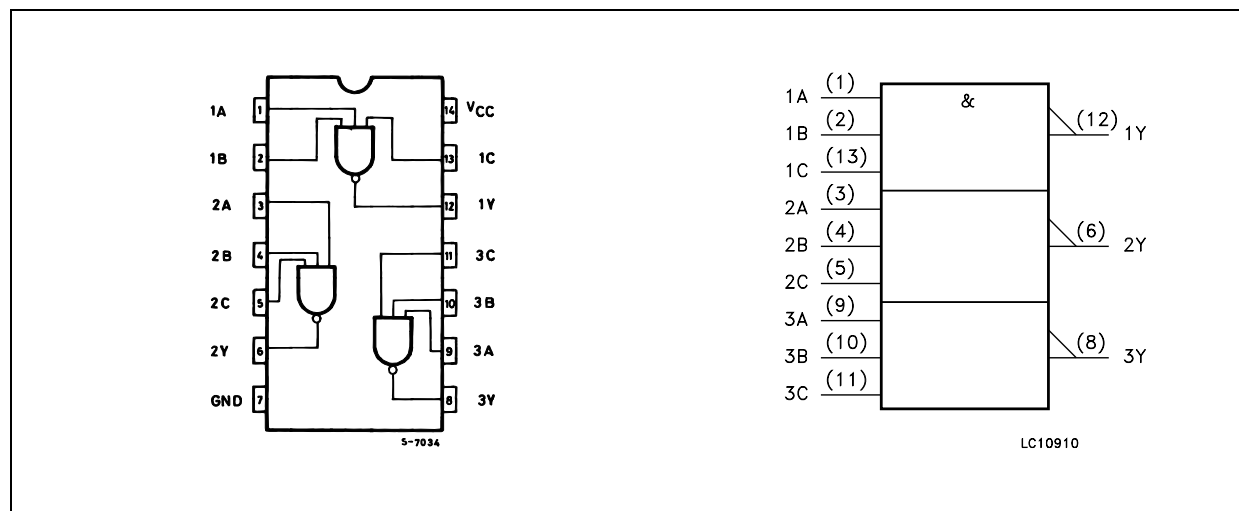
| PACKAGE | TUBE | T & R |
|---------|----------|------------|
| SOP | 74LVQ10M | 74LVQ10MTR |
| TSSOP | | 74LVQ10TTR |

technology. It is ideal for low power and low noise 3.3V applications.

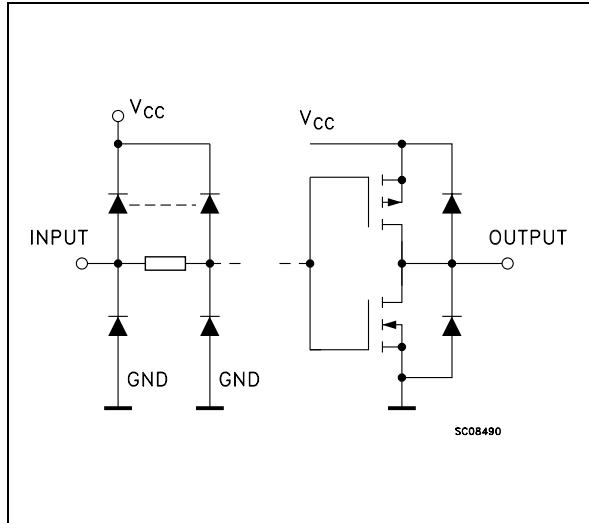
The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

| PIN No | SYMBOL | NAME AND FUNCTION |
|-----------|-----------------|-------------------------|
| 1, 3, 9 | 1A to 3A | Data Inputs |
| 2, 4, 10 | 1B to 3B | Data Inputs |
| 13, 5, 11 | 1C to 3C | Data Inputs |
| 12, 6, 8 | 1Y to 3Y | Data Outputs |
| 7 | GND | Ground (0V) |
| 14 | V _{CC} | Positive Supply Voltage |

TRUTH TABLE

| A | B | C | Y |
|---|---|---|---|
| L | X | X | H |
| X | L | X | H |
| X | X | L | H |
| H | H | H | L |

ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|-------------------------------------|--------------------------------------|-------------------------------|------|
| V _{CC} | Supply Voltage | -0.5 to +7 | V |
| V _I | DC Input Voltage | -0.5 to V _{CC} + 0.5 | V |
| V _O | DC Output Voltage | -0.5 to V _{CC} + 0.5 | V |
| I _{IK} | DC Input Diode Current | ± 20 | mA |
| I _{OK} | DC Output Diode Current | ± 20 | mA |
| I _O | DC Output Current | ± 50 | mA |
| I _{CC} or I _{GND} | DC V _{CC} or Ground Current | ± 150 | mA |
| T _{stg} | Storage Temperature | -65 to +150 | °C |
| T _L | Lead Temperature (10 sec) | 300 | °C |

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Value | Unit |
|-----------------|--|----------------------|------|
| V _{CC} | Supply Voltage (note 1) | 2 to 3.6 | V |
| V _I | Input Voltage | 0 to V _{CC} | V |
| V _O | Output Voltage | 0 to V _{CC} | V |
| T _{op} | Operating Temperature | -55 to 125 | °C |
| dt/dv | Input Rise and Fall Time V _{CC} = 3.0V (note 2) | 0 to 10 | ns/V |

1) Truth Table guaranteed: 1.2V to 3.6V

2) V_{IN} from 0.8V to 2V

DC SPECIFICATIONS

| Symbol | Parameter | Test Condition | | Value | | | | | | Unit | |
|------------------|------------------------------------|------------------------|---|-----------------------|-------|-------|-------------|------|--------------|------|------|
| | | V _{CC} (V) | | T _A = 25°C | | | -40 to 85°C | | -55 to 125°C | | |
| | | | | Min. | Typ. | Max. | Min. | Max. | Min. | | Max. |
| V _{IH} | High Level Input Voltage | 3.0 to 3.6 | | 2.0 | | | 2.0 | | 2.0 | | V |
| V _{IL} | Low Level Input Voltage | | | | | 0.8 | | 0.8 | | 0.8 | V |
| V _{OH} | High Level Output Voltage | 3.0 | I _O =-50 μA | 2.9 | 2.99 | | 2.9 | | 2.9 | | V |
| | | | I _O =-12 mA | 2.58 | | | 2.48 | | 2.48 | | |
| | | | I _O =-24 mA | | | | 2.2 | | 2.2 | | |
| V _{OL} | Low Level Output Voltage | 3.0 | I _O =50 μA | | 0.002 | 0.1 | | 0.1 | | 0.1 | V |
| | | | I _O =12 mA | | 0 | 0.36 | | 0.44 | | 0.44 | |
| | | | I _O =24 mA | | | | | 0.55 | | 0.55 | |
| I _I | Input Leakage Current | 3.6 | V _I = V _{CC} or GND | | | ± 0.1 | | ± 1 | | ± 1 | μA |
| I _{CC} | Quiescent Supply Current | 3.6 | V _I = V _{CC} or GND | | | 2 | | 20 | | 20 | μA |
| I _{OLD} | Dynamic Output Current (note 1, 2) | 3.6 | V _{OLD} = 0.8 V max | | | | 36 | | 25 | | mA |
| I _{OHD} | | | V _{OHD} = 2 V min | | | | -25 | | -25 | | mA |

1) Maximum test duration 2ms, one output loaded at time

2) Incident wave switching is guaranteed on transmission lines with impedances as low as 75Ω

DYNAMIC SWITCHING CHARACTERISTICS

| Symbol | Parameter | Test Condition | | Value | | | | | | Unit | |
|------------------|--|------------------------|------------------------|-----------------------|------|------|-------------|------|--------------|------|------|
| | | V _{CC} (V) | | T _A = 25°C | | | -40 to 85°C | | -55 to 125°C | | |
| | | | | Min. | Typ. | Max. | Min. | Max. | Min. | | Max. |
| V _{OLP} | Dynamic Low Voltage Quiet Output (note 1, 2) | 3.3 | C _L = 50 pF | | 0.3 | 0.8 | | | | | V |
| V _{OLV} | | | | -0.8 | -0.3 | | | | | | |
| V _{IHD} | Dynamic High Voltage Input (note 1, 3) | 3.3 | | 2 | | | | | | | V |
| V _{ILD} | Dynamic Low Voltage Input (note 1, 3) | 3.3 | | | | 0.8 | | | | | V |

1) Worst case package.

2) Max number of outputs defined as (n). Data inputs are driven 0V to 3.3V, (n-1) outputs switching and one output at GND.

3) Max number of data inputs (n) switching. (n-1) switching 0V to 3.3V. Inputs under test switching: 3.3V to threshold (V_{ILD}), 0V to threshold (V_{IHD}), f=1MHz.

74LVQ10

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, $R_L = 500 \Omega$, Input $t_r = t_f = 3 \text{ ns}$)

| Symbol | Parameter | Test Condition | | Value | | | | | | Unit | |
|--------------------------|---------------------------------------|-----------------|--|--------------------------|------|------|------------------------------------|------|-------------------------------------|------|------|
| | | V_{CC} (V) | | $T_A = 25^\circ\text{C}$ | | | $-40 \text{ to } 85^\circ\text{C}$ | | $-55 \text{ to } 125^\circ\text{C}$ | | |
| | | | | Min. | Typ. | Max. | Min. | Max. | Min. | | Max. |
| t_{PLH} t_{PHL} | Propagation Delay Time | 2.7 | | . | 6.0 | 10.0 | | 11.5 | | 13.0 | ns |
| | | 3.3(*) | | | 5.3 | 8.0 | | 9.0 | | 10.5 | |
| t_{OSLH} t_{OSHL} | Output To Output Skew Time (note1, 2) | 2.7 | | | 0.5 | 1.0 | | 1.0 | | 1.0 | ns |
| | | 3.3(*) | | | 0.5 | 1.0 | | 1.0 | | 1.0 | |

1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW ($t_{OSLH} = |t_{PLHm} - t_{PLHn}|$, $t_{OSHL} = |t_{PHLm} - t_{PHLn}|$)

2) Parameter guaranteed by design

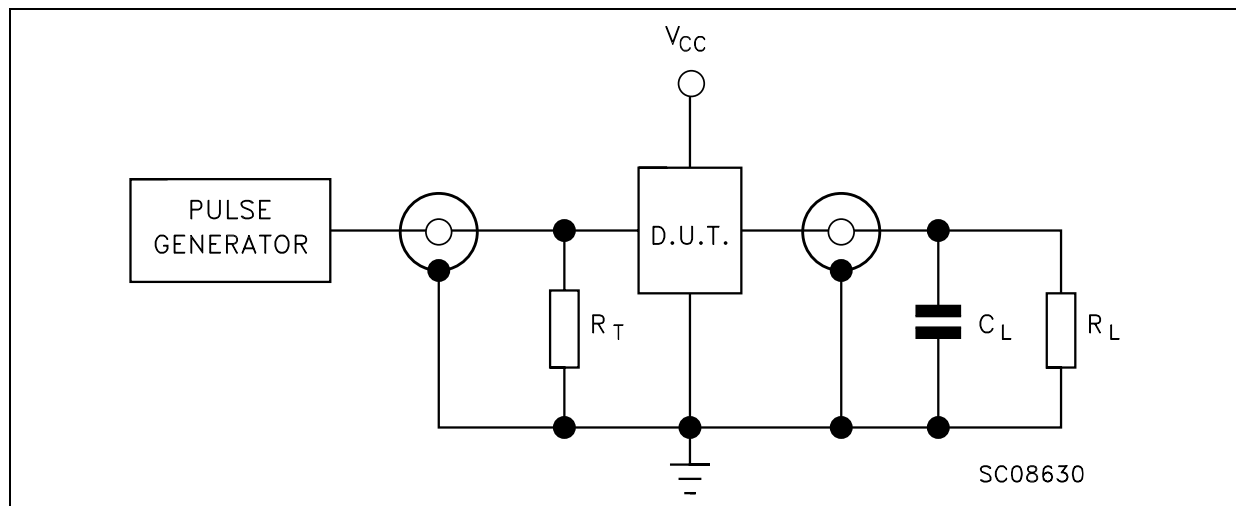
(*) Voltage range is $3.3\text{V} \pm 0.3\text{V}$

CAPACITIVE CHARACTERISTICS

| Symbol | Parameter | Test Condition | | Value | | | | | | Unit | |
|----------|--|-----------------|-------------------------|--------------------------|------|------|------------------------------------|------|-------------------------------------|------|------|
| | | V_{CC} (V) | | $T_A = 25^\circ\text{C}$ | | | $-40 \text{ to } 85^\circ\text{C}$ | | $-55 \text{ to } 125^\circ\text{C}$ | | |
| | | | | Min. | Typ. | Max. | Min. | Max. | Min. | | Max. |
| C_{IN} | Input Capacitance | 3.3 | | | 4 | | | | | | pF |
| C_{PD} | Power Dissipation Capacitance (note 1) | 3.3 | $f_{IN} = 10\text{MHz}$ | | 30 | | | | | | pF |

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/n$ (per circuit)

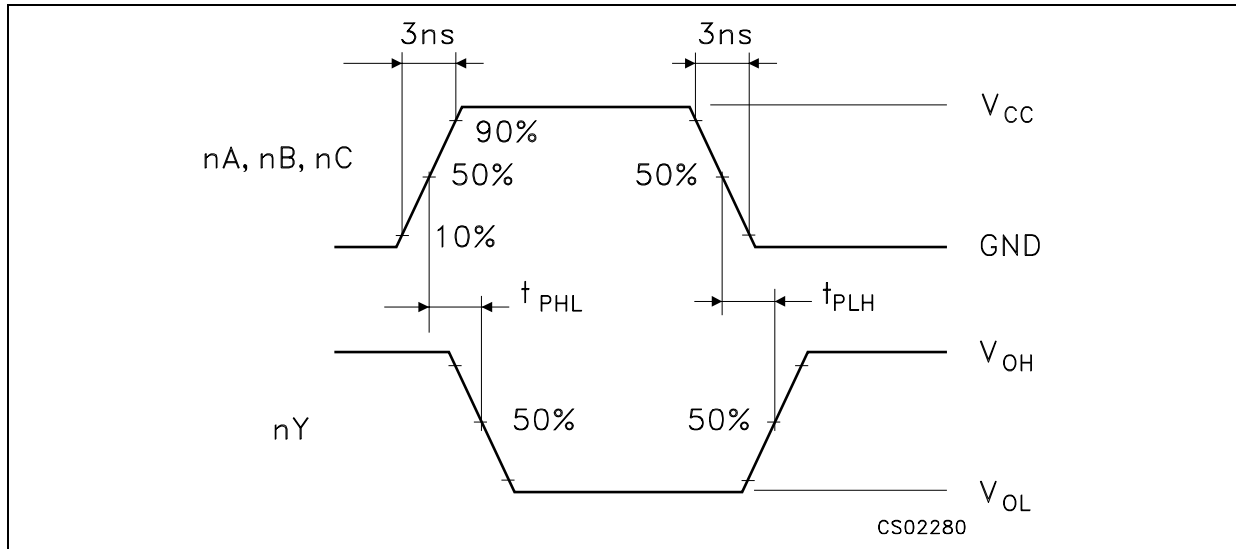
TEST CIRCUIT



$C_L = 50 \text{ pF}$ or equivalent (includes jig and probe capacitance)

$R_L = 500 \Omega$ or equivalent

$R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

WAVEFORM: PROPAGATION DELAYS ($f=1\text{MHz}$; 50% duty cycle)

SO-14 MECHANICAL DATA

| DIM. | mm. | | | inch | | |
|------|------------|------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | | | 1.75 | | | 0.068 |
| a1 | 0.1 | | 0.2 | 0.003 | | 0.007 |
| a2 | | | 1.65 | | | 0.064 |
| b | 0.35 | | 0.46 | 0.013 | | 0.018 |
| b1 | 0.19 | | 0.25 | 0.007 | | 0.010 |
| C | | 0.5 | | | 0.019 | |
| c1 | 45° (typ.) | | | | | |
| D | 8.55 | | 8.75 | 0.336 | | 0.344 |
| E | 5.8 | | 6.2 | 0.228 | | 0.244 |
| e | | 1.27 | | | 0.050 | |
| e3 | | 7.62 | | | 0.300 | |
| F | 3.8 | | 4.0 | 0.149 | | 0.157 |
| G | 4.6 | | 5.3 | 0.181 | | 0.208 |
| L | 0.5 | | 1.27 | 0.019 | | 0.050 |
| M | | | 0.68 | | | 0.026 |
| S | 8° (max.) | | | | | |



PO13G

TSSOP14 MECHANICAL DATA

| DIM. | mm. | | | inch | | |
|------|------|----------|------|-------|------------|--------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | | | 1.2 | | | 0.047 |
| A1 | 0.05 | | 0.15 | 0.002 | 0.004 | 0.006 |
| A2 | 0.8 | 1 | 1.05 | 0.031 | 0.039 | 0.041 |
| b | 0.19 | | 0.30 | 0.007 | | 0.012 |
| c | 0.09 | | 0.20 | 0.004 | | 0.0089 |
| D | 4.9 | 5 | 5.1 | 0.193 | 0.197 | 0.201 |
| E | 6.2 | 6.4 | 6.6 | 0.244 | 0.252 | 0.260 |
| E1 | 4.3 | 4.4 | 4.48 | 0.169 | 0.173 | 0.176 |
| e | | 0.65 BSC | | | 0.0256 BSC | |
| K | 0° | | 8° | 0° | | 8° |
| L | 0.45 | 0.60 | 0.75 | 0.018 | 0.024 | 0.030 |



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